Zibo Seno Electronic Engineering Co., Ltd.



GBJ8005 - GBJ810





8.0A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V_{RMS}
- Low Reverse Leakage Current
- Surge Overload Rating to 170A Peak
- Ideal for Printed Circuit Board Applications
- Plastic Material UL Flammability Classification 94V-0
- Lead Free:For RoHS / Lead Free Version

9504								
Dim	Min	Max						
Α	24.80	25.20						
В	14.70	15.30						
С	4.00 Nominal							
D	17.20	17.80						
E	0.90	1.10						
G	7.30	7.70						
Н	3.10 Ø	3.40 ∅						
J	3.30	3.70						
K	1.50	1.90						
L	9.30	9.70						
М	2.50	2.90						
N	3.40	3.80						
Р	4.40	4.80						
R	0.60	0.80						
All Dimensions in mm								

GBJ4

Mechanical Data

Case: Molded Plastic

 Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208

Polarity: Molded on Body

Mounting: Through Hole for #6 ScrewMounting Torque: 5.0 in-lbs Maximum

Weight: 6.6 grams (approx)Marking: Type Number

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GBJ 8005	GBJ 801	GBJ 802	GBJ 804	GBJ 806	GBJ 808	GBJ 810	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Forward Rectified Output Current @ T _C = 110°C	lo	8.0							Α
Non-Repetitive Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load		170						Α	
Forward Voltage per element @ I _F = 4.0A	V _{FM}	1.0						V	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		5.0 500						μА	
I ² t Rating for Fusing (t < 8.3ms) (Note 1)		120						A ² s	
Typical Total Capacitance per Element (Note 2)		55						pF	
Typical Thermal Resistance Junction to Case (Note 3)		1.6						°C/W	
Operating and Storage Temperature Range		-65 to +150						°C	

Notes:

- 1. Non-repetitive, for t > 1.0ms and < 8.3ms.
- Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
- 3. Thermal resistance from junction to case per element. Unit mounted on 100 x 100 x 1.6mm aluminum plate heat sink.
- 4. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.

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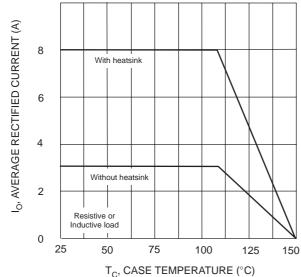
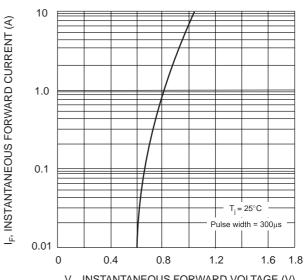


Fig. 1 Forward Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics (per element)

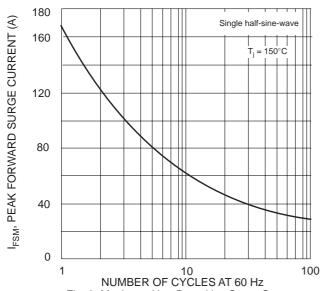


Fig. 3 Maximum Non-Repetitive Surge Current

